

Lecture 18

OUTLINE

- Basic MOSFET amplifier
- MOSFET biasing
- MOSFET current sources
- Common-source amplifier

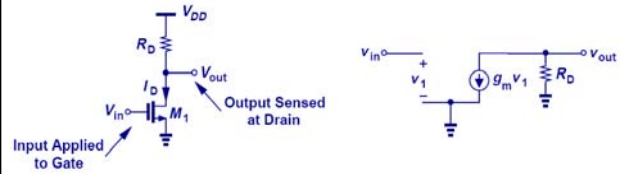
- Reading: Chap. 7.1-7.2

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Common-Source Stage



$$\lambda = 0$$

$$A_v = -g_m R_D$$

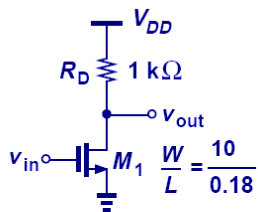
$$A_v = -\sqrt{2\mu_n C_{ox} \frac{W}{L}} I_D R_D$$

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Operation in Saturation



Condition for M_1 in saturation

$$V_{out} > V_{in} - V_{TH}$$

$$\Rightarrow V_{DD} - R_D I_D > (V_{GS} - V_{TH})$$

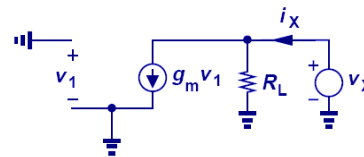
- In order to maintain operation in saturation, V_{out} cannot fall below V_{in} by more than one threshold voltage.
- The condition above ensures operation in saturation.

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CS Stage with $\lambda=0$



$$A_v = -g_m R_L$$

$$R_{in} = \infty$$

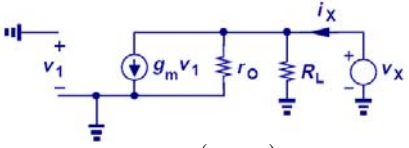
$$R_{out} = R_L$$

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CS Stage with $\lambda \neq 0$



$$A_v = -g_m(R_L \parallel r_o)$$

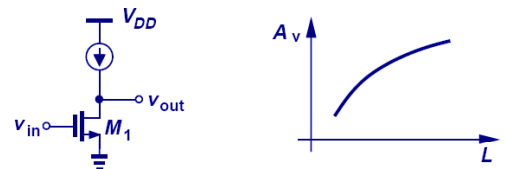
$$R_{in} = \infty$$

$$R_{out} = R_L \parallel r_o$$

- However, channel length modulation leads to finite output resistance, r_o , which is in parallel with the load resistance, R_L

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CS Gain Variation with Channel Length

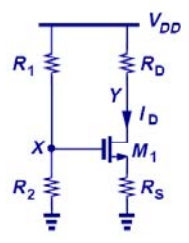


$$|A_v| = \frac{\sqrt{2\mu_n C_{ox} \frac{W}{L}}}{\lambda \sqrt{I_D}} \propto \sqrt{\frac{2\mu_n C_{ox} WL}{I_D}}$$

- Since λ is inversely proportional to L , the intrinsic voltage gain actually becomes proportional to the square root of L .

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MOS Biasing



$$\frac{R_1}{R_1 + R_2} V_{DD} = V_{GS} + I_D R_S$$

$$I_D = \frac{1}{2} \mu_n C_{ox} \frac{W}{L} (V_{GS} - V_{TH})^2$$

2 unknowns (V_{GS} , I_D), 2 equations \Rightarrow

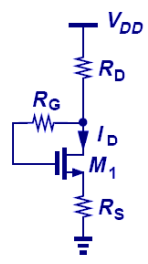
$$V_{GS} = -(V_1 - V_{TH}) + \sqrt{V_1^2 + 2V_1 \left(\frac{R_1 V_{DD}}{R_1 + R_2} - V_{TH} \right)}$$

$$V_1 = \frac{1}{\mu_n C_{ox} \frac{W}{L} R_S}$$

- Voltage at X is determined by V_{DD} , R_1 , and R_2 .
- V_{GS} can be found using the equation above, and I_D can be found by using the NMOS current equation.

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Self-Biased MOS Stage



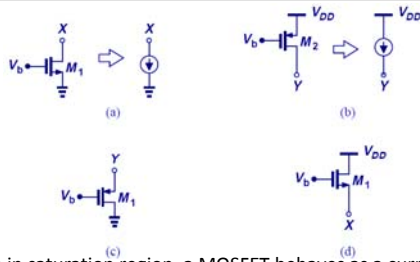
$$I_D R_D + V_{GS} + R_S I_D = V_{DD}$$

$$I_D = \frac{1}{2} \mu_n C_{ox} \frac{W}{L} (V_{GS} - V_{TH})^2$$

- The circuit above is analyzed by noting M_1 is in saturation and no potential drop appears across R_G .

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Current Sources



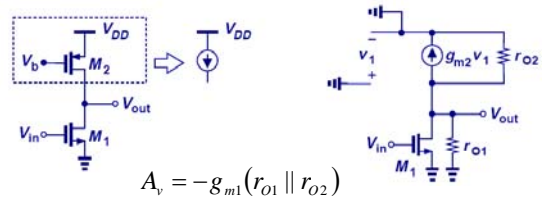
- When in saturation region, a MOSFET behaves as a current source.
- NMOS draws current from a point to ground (sinks current), whereas PMOS draws current from V_{DD} to a point (sources current).

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CS Stage with Current-Source Load



$$A_v = -g_{m1}(r_{O1} \parallel r_{O2})$$

$$R_{out} = r_{O1} \parallel r_{O2}$$

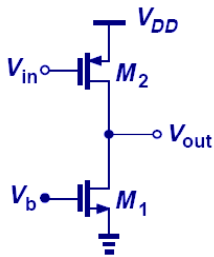
- To alleviate the headroom problem, an active current-source load is used.
- This is advantageous because a current-source has a high output resistance and can tolerate a small voltage drop across it.

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PMOS CS Stage with NMOS as Load



$$A_v = -g_{m2}(r_{O1} \parallel r_{O2})$$

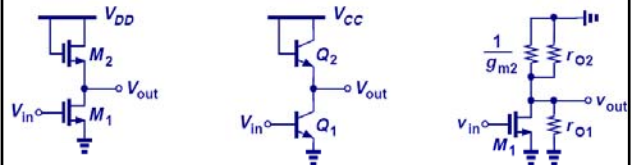
- Similarly, with PMOS as input stage and NMOS as the load, the voltage gain is the same as before.

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CS Stage with Diode-Connected Load



$$A_v = -g_{m1} \left(\frac{1}{g_{m2}} \parallel r_{O2} \parallel r_{O1} \right)$$

$$A_v = -g_{m1} \cdot \frac{1}{g_{m2}} = -\sqrt{\frac{(W/L)_1}{(W/L)_2}}$$

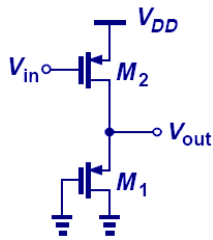
- Lower gain, but less dependent on process parameters.

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CS Stage with Diode-Connected PMOS Device



$$A_v = -g_{m2} \left(\frac{1}{g_{m1}} \parallel r_{o1} \parallel r_{o2} \right)$$

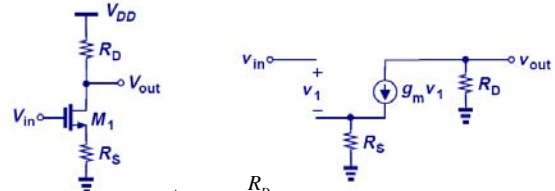
- Note that PMOS circuit symbol is usually drawn with the source on top of the drain.

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CS Stage with Degeneration



$$A_v = -\frac{R_D}{\frac{1}{g_m} + R_S}$$

$$\lambda = 0$$

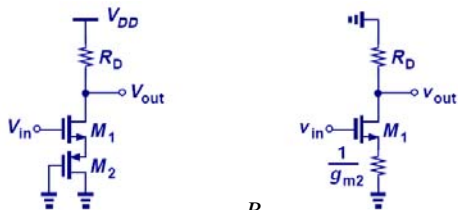
- Similar to bipolar counterpart, when a CS stage is degenerated, its gain, I/O impedances, and linearity change.

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Example of CS Stage with Degeneration



$$A_v = -\frac{R_D}{\frac{1}{g_{m1}} + \frac{1}{g_{m2}}}$$

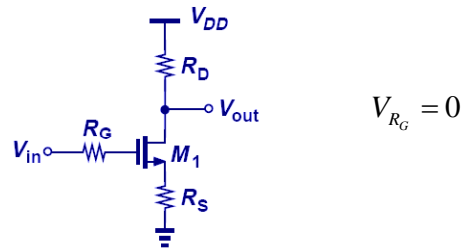
- A diode-connected device degenerates a CS stage.

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CS Stage with Gate Resistance



$$V_{R_G} = 0$$

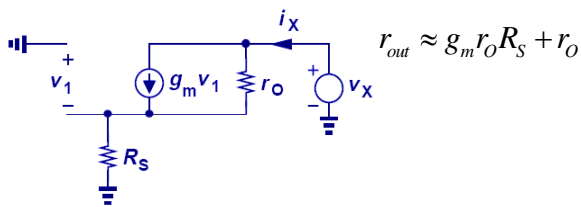
- Since at low frequencies, the gate conducts no current, gate resistance does not affect the gain or I/O impedances.

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Output Impedance of CS Stage with Degeneration



$$r_{out} \approx g_m r_O R_S + r_O$$

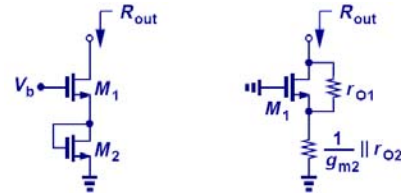
- Similar to the bipolar counterpart, degeneration boosts output impedance.

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Output Impedance Example (I)



$$R_{out} = r_{O1} \left(1 + g_{m1} \frac{1}{g_{m2}} \right)$$

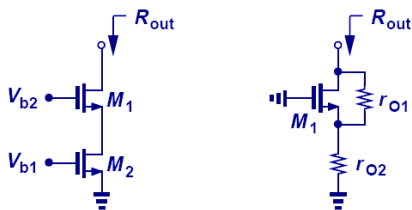
- When $1/g_m$ is parallel with r_{O2} , we often just consider $1/g_m$

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Output Impedance Example (II)



$$R_{out} \approx g_{m1} r_{O1} r_{O2} + r_{O1}$$

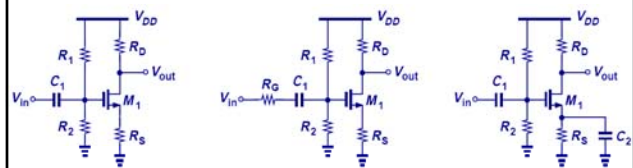
- In this example, the impedance that degenerates the CS stage is r_{O2} , instead of $1/g_m$ in the previous example.

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CS Core with Biasing



$$A_v = \frac{R_1 \parallel R_2}{R_G + R_1 \parallel R_2} \cdot \frac{-R_D}{\frac{1}{g_m} + R_S}$$

$$A_v = -g_m R_D$$

- Degeneration is used to stabilize bias point, and a bypass capacitor can be used to obtain a larger small-signal voltage gain at the frequency of interest.

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